

UNISONIC TECHNOLOGIES CO., LTD

## DTB114E

### PNP SILICON TRANSISTOR

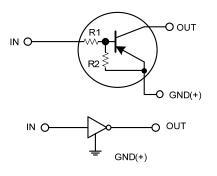
# DIGITAL TRANSISTORS (BUILT-IN BIAS RESISTORS)

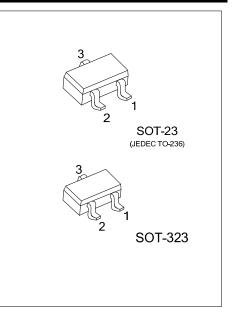
#### FEATURES

\* Built-in bias resistors that implies easy ON/OFF applications.

\* The bias resistors are thin-film resistors with complete isolation to allow positive input.

#### EQUIVALENT CIRCUIT





#### ORDERING INFORMATION

Ordering Number	Package	Pin Assignment			Decking	
		1	2	3	Packing	
DTB114EG-AE3-R	SOT-23	G	I	0	Tape Reel	
DTB114EG-AL3-R	SOT-323	G	I	0	Tape Reel	
					•	

Note: Pin Assignment: G: GND I: IN O: OUT

DTB114EG- <u>AE3-</u> R	1)Packing Type	(1) R: Tape Reel
	2)Package Type	(2) AE3: SOT-23, AL3: SOT-323
(3	3)Green Package	(3) G: Halogen Free and Lead Free

#### MARKING



#### ■ ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C, unless otherwise specified)

PARAMETER	SYMBOL RATING		UNIT
Supply Voltage	V <sub>cc</sub>	-50	V
Input Voltage	V <sub>IN</sub>	-40~+10	V
Output Current	I <sub>OUT</sub>	-500	mA
Power Dissipation	PD	200	
Junction Temperature	TJ	150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

## ■ ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C, unless otherwise specified.)

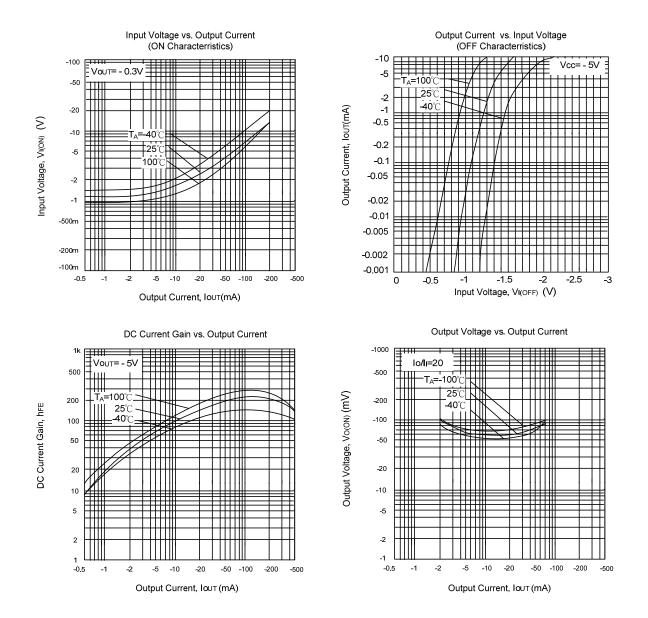
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Input Voltage	V <sub>IN(OFF)</sub>	V <sub>CC</sub> = -5V, Ι <sub>ΟUT</sub> = -100μΑ			-0.5	V
	V <sub>IN(ON)</sub>	V <sub>OUT</sub> = -0.3V, I <sub>OUT</sub> = -10mA	-3			V
Output Voltage	V <sub>OUT(ON)</sub>	I <sub>OUT</sub> /I <sub>IN</sub> = -50mA/-2.5 mA		-0.1	-0.3	V
Input Current	I <sub>IN</sub>	V <sub>IN</sub> = -5V			-0.88	mA
Output Current	I <sub>OUT(OFF)</sub>	V <sub>CC</sub> = -50V , V <sub>IN</sub> =0V			-0.5	μA
DC Current Gain	h <sub>FE</sub>	V <sub>OUT</sub> = -5V, I <sub>OUT</sub> = -50mA	56			
Input Resistance	R <sub>1</sub>		7	10	13	kΩ
Resistance Ratio	$R_2/R_1$		0.8	1	1.2	
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> = -10 V, I <sub>E</sub> =5mA, f=100MHz(Note)		200		MHz

Note: Transition frequency of the device



# DTB114E

#### TYPICAL CHARACTERISTICS



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.

